

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}TYP$	I_D
-100V	9mΩ@-10V	-150A



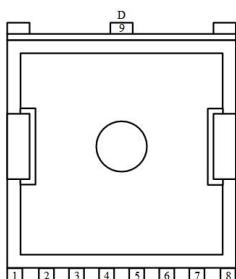
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Advanced Split Gate Trench Technology
- 100% Single Pulse avalanche energy Test

Applications

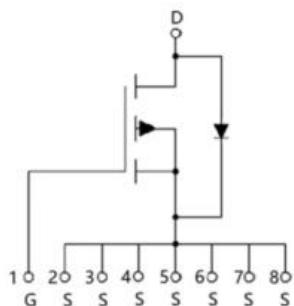
- PWM Application
- Hard switched and high frequency circuits
- Power Management

Package

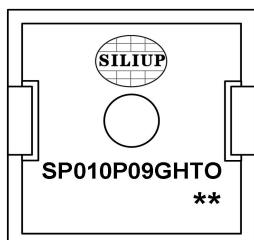


TOLL

Circuit diagram



Marking



SP010P09GHTO :Device Code
** :Week Code

Order Information

Device	Package	Unit/Tape
SP010P09GHTO	TOLL	2000

Absolute maximum ratings (Ta=25°C,unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V _{DS}	-100	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current(Tc=25°C)	I _D	-150	A
Continuous Drain Current(Tc=100°C)	I _D	-100	A
Pulsed Drain Current	I _{DM}	-600	A
Single Pulse Avalanche Energy ¹	E _{AS}	1025	mJ
Power Dissipation(Tc=25°C)	P _D	290	W
Thermal Resistance Junction-to-Case	R _{θJC}	0.43	°C/W
Storage Temperature Range	T _{STG}	-55 to 150	°C
Operating Junction Temperature Range	T _J	-55 to 150	°C

Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V , ID= -250uA	-100	-110	-	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =-80V , V _{GS} =0V , TJ=25°C	-	-	-1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±20V , V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{GS} =V _{DS} , ID = -250uA	-2	-3	-4	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-10V , ID= -20A	-	9	11	mΩ
Dynamic characteristics						
Input Capacitance	C _{iss}	VDS=-50V , VGS=0V , f=1MHz	-	13600	-	pF
Output Capacitance	C _{oss}		-	1200	-	
Reverse Transfer Capacitance	C _{rss}		-	26	-	
Total Gate Charge	Q _g	VDS=-50V , VGS=10V , ID=-20A	-	168	-	nC
Gate-Source Charge	Q _{gs}		-	46	-	
Gate-Drain Charge	Q _{gd}		-	23	-	
Switching Characteristics						
Turn-On Delay Time	T _{d(on)}	VDD=-50V , VGS=10V , RG=1.6Ω, ID=-20A	-	16	-	nS
Rise Time	T _r		-	58	-	
Turn-Off Delay Time	T _{d(off)}		-	145	-	
Fall Time	T _f		-	56	-	
Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V , I _s =-1A , TJ=25°C	-	-	-1.2	V
Maximum Body-Diode Continuous Current	I _s		-	-	-150	A
Reverse Recovery Time	T _{rr}	I _s =-20A, di/dt=100A/us, TJ=25°C	-	96	-	nS
Reverse Recovery Charge	Q _{rr}		-	205	-	nC

Note :

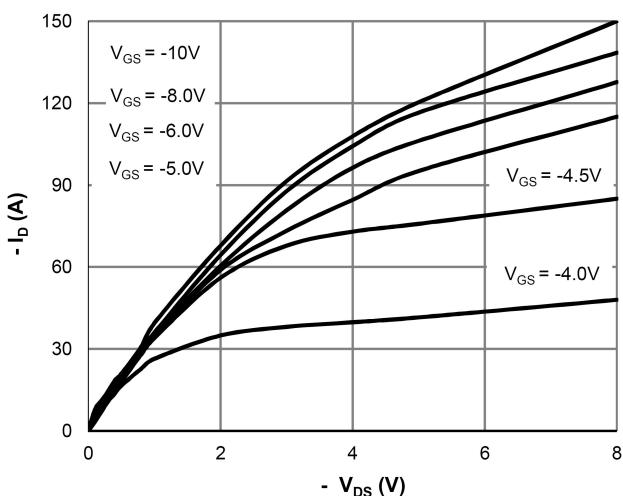
1. The test condition is VDD=-50V,VGS=-10V,L=0.5mH,RG=25Ω



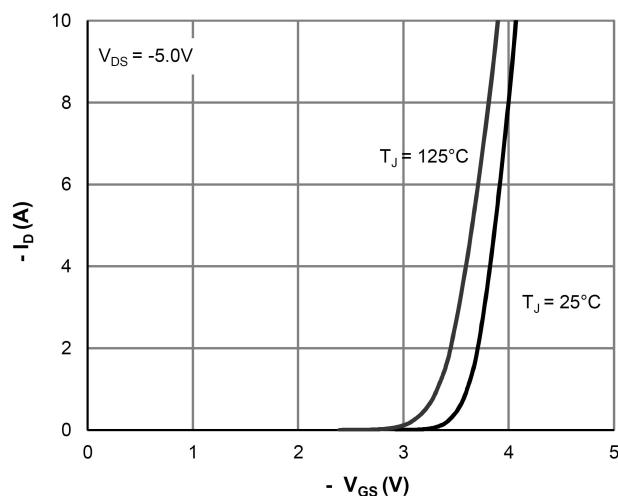
Typical Characteristics

SP010P09GHTO

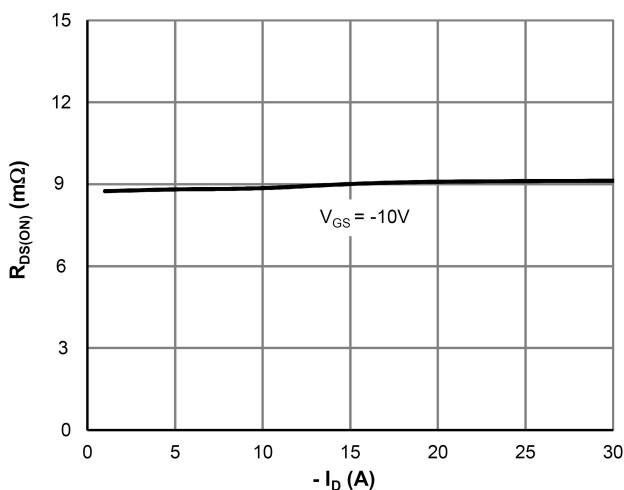
100V P-Channel Power MOSFET



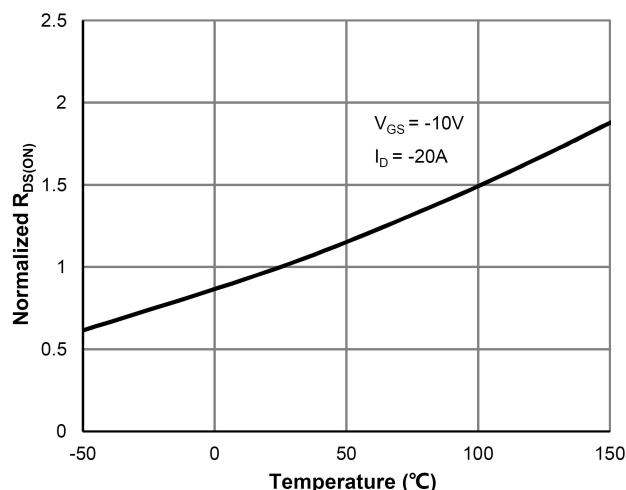
Saturation Characteristics



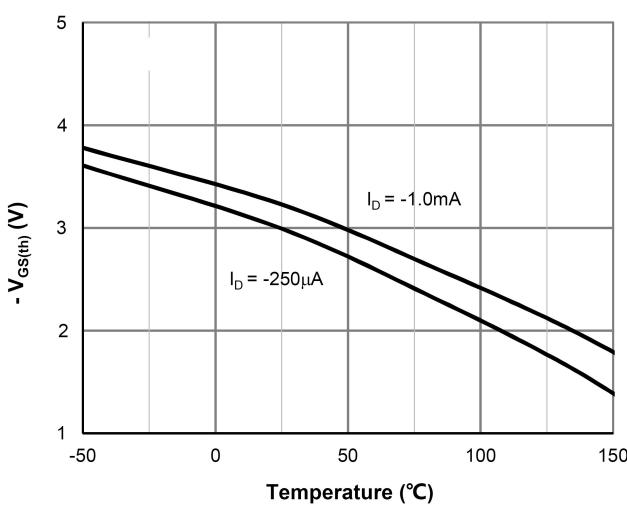
Transfer Characteristics



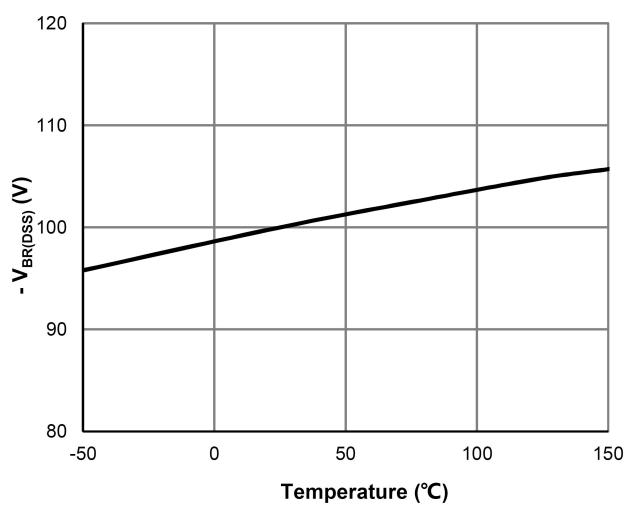
$R_{DS(ON)}$ vs. Drain Current



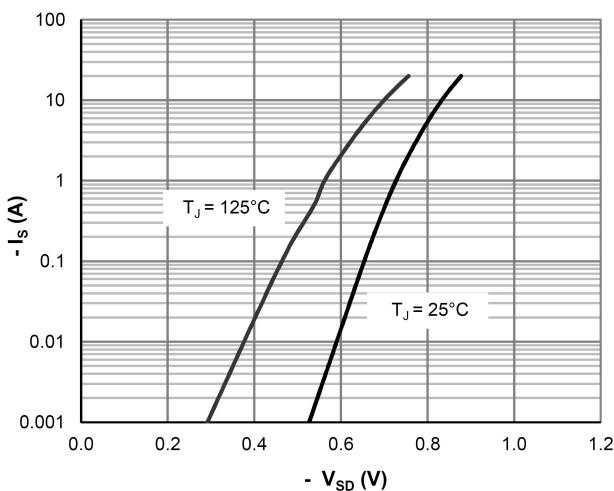
$R_{DS(ON)}$ vs. Junction Temperature



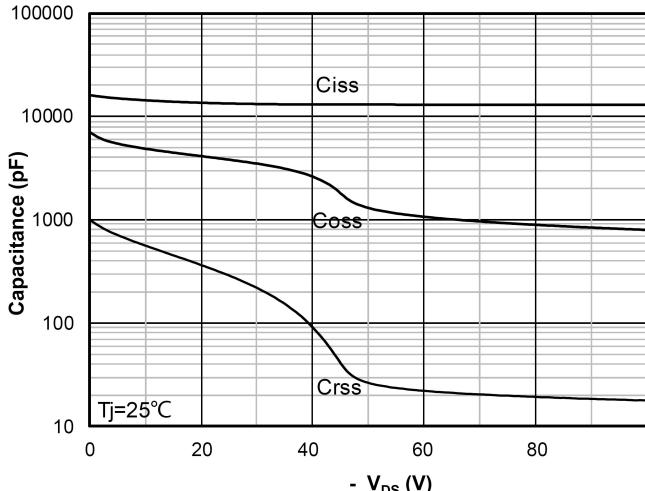
$V_{GS(th)}$ vs. Junction Temperature



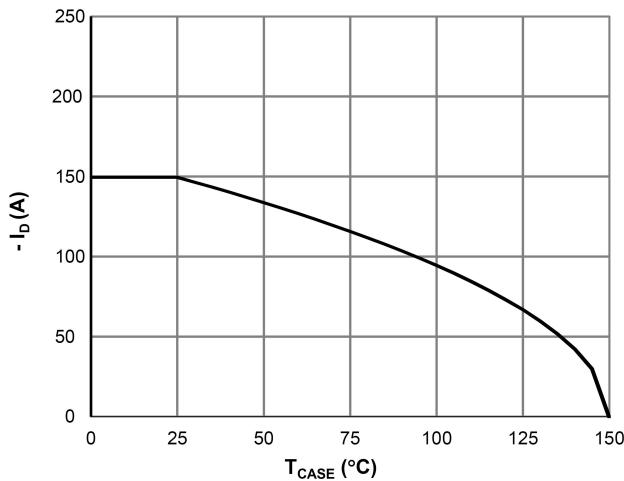
$V_{BR(DSS)}$ vs. Junction Temperature



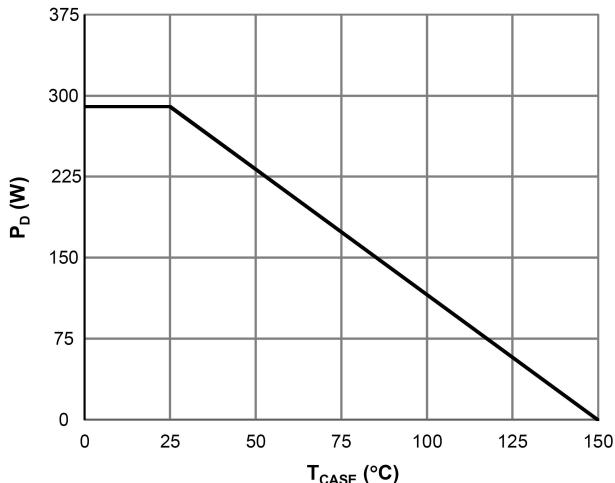
Body-Diode Characteristics



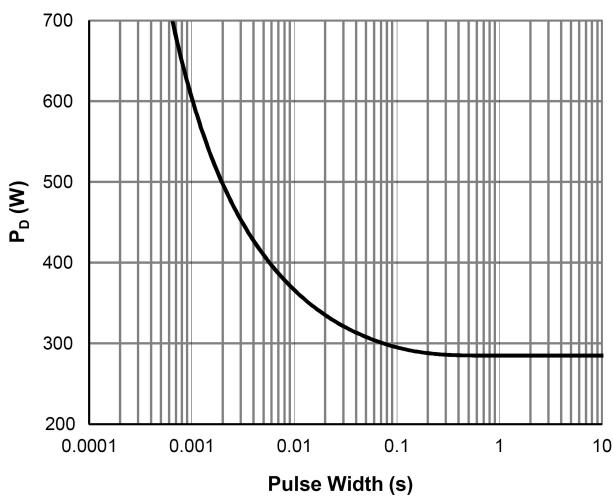
Capacitance Characteristics



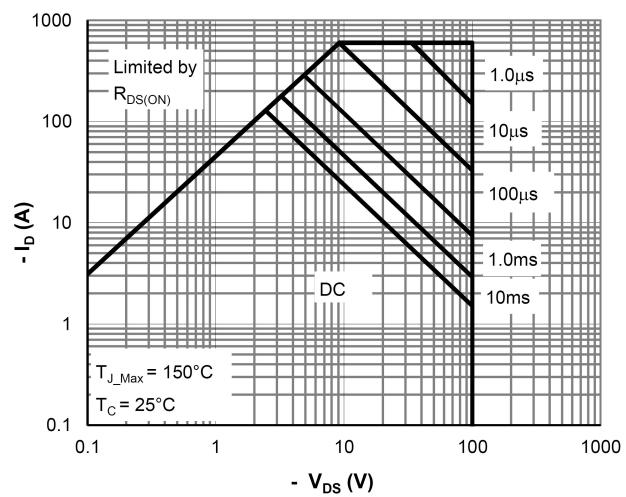
Current De-rating



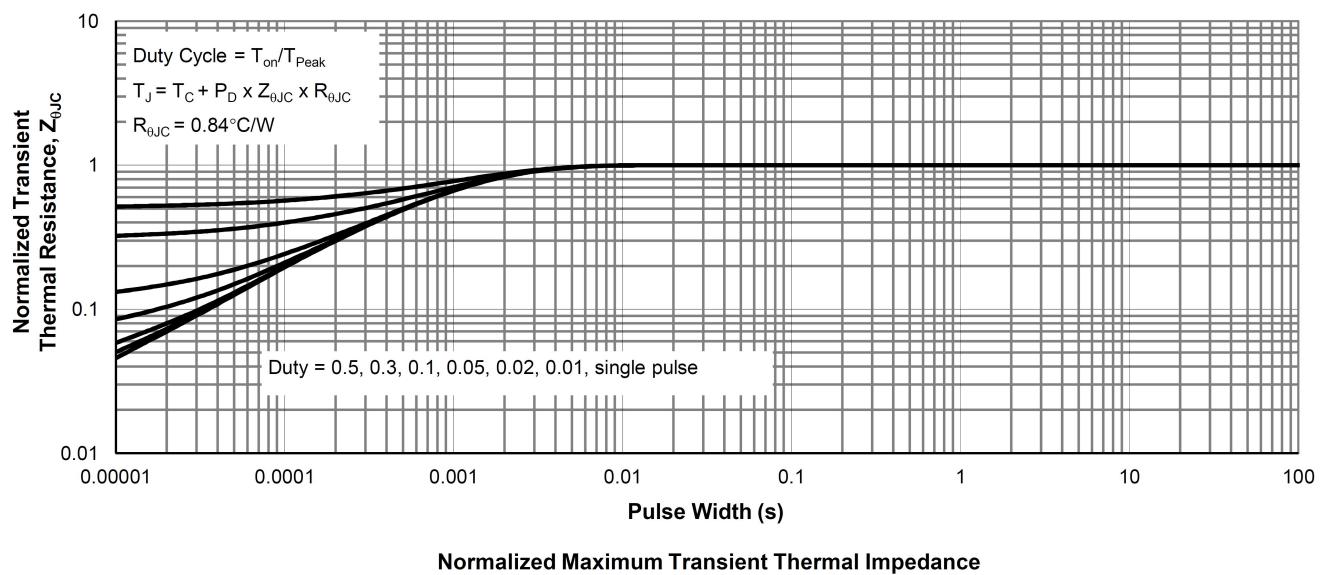
Power De-rating

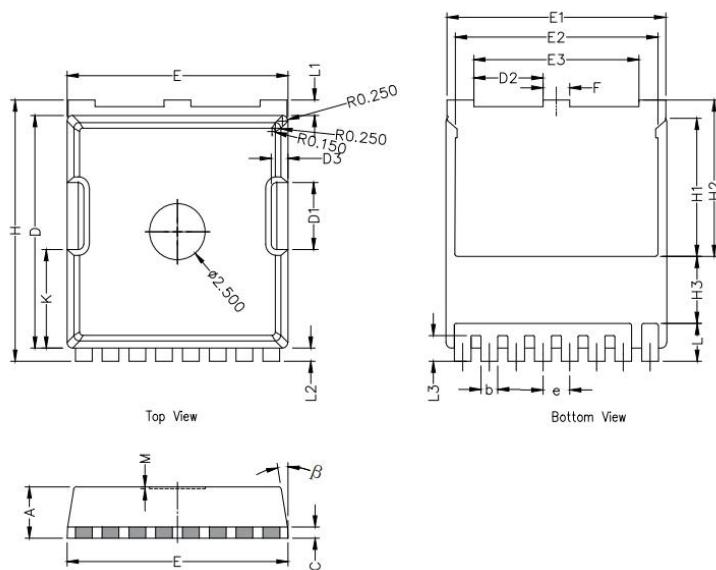


Single Pulse Power Rating, Junction-to-Case



Maximum Safe Operating Area



TOLL Package Information


Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	2.20	2.30	2.40
b	0.65	0.75	0.85
C	0.508 REF		
D	10.25	10.40	10.55
D1	2.85	3.00	3.15
E	9.75	9.90	10.05
E1	9.65	9.80	9.95
E2	8.95	9.10	9.25
E3	7.25	7.40	7.55
e	1.20 BSC		
F	1.05	1.20	1.35
H	11.55	11.70	11.85
H1	6.03	6.18	6.33
H2	6.85	7.00	7.15
H3	3.00 BSC		
L	1.55	1.70	1.85
L1	0.55	0.7	0.85
L2	0.45	0.6	0.75
M	0.08 REF.		
β	8°	10°	12°
K	4.25	4.40	4.55